

DRIC-DVC-102

3 Channel D/R Integrated Circuit

FEATURES

- Programmable Time Delay of Analog Signals
- Capture and Loop Playback after Trigger
- Up To 3 Analog Channels
- Playback Data At Reduced Rates
- 175 ms Maximum Delay With External Memory
- Single 5 Volt Supply
- 100 Lead Thin Quad Flat Pack
- Available In Die Form

APPLICATIONS

- Munitions Testing
- Industrial Instrumentation
- Store And Forward Data Acquisition
- System Health Monitoring

GENERAL DESCRIPTION

The 3 Channel Delay/Repeater (D/R) IC provides three channels of delayed or delayed and repeated analog signals with a bandwidth range of 0 to 60 KHz. The D/R provides up to 20 ms of time delay in 5 ms increments on-chip. A maximum delay of 175 ms can be supported using an external commercial-off-the-shelf (COTS) SRAM.

A block diagram of the 3 Channel D/R IC is shown in Figure 1. It uses a mixed signal implementation where three independent analog-to-digital (A/D) converters with 12-bit accuracy are used to sample the input signal waveform. The 60 KHz signal bandwidth is approximately 40 percent of the sample rate. This meets the Nyquist criteria and allows for anti-alias filter rolloff.

The digitized outputs of the A/D converters (12 bits at 150 KSPS) are bussed and written to the internal memory (3 channels x 12 bits x 150 KSPS x 0.02 sec = 108 Kbits) or external memory interface (256K x 8 bits SRAM).

After the data is read from memory, it is fed into three independent digital-to-analog (D/A) converters for signal reconstruction. Output filters remove spurs generated by the D/A converters.

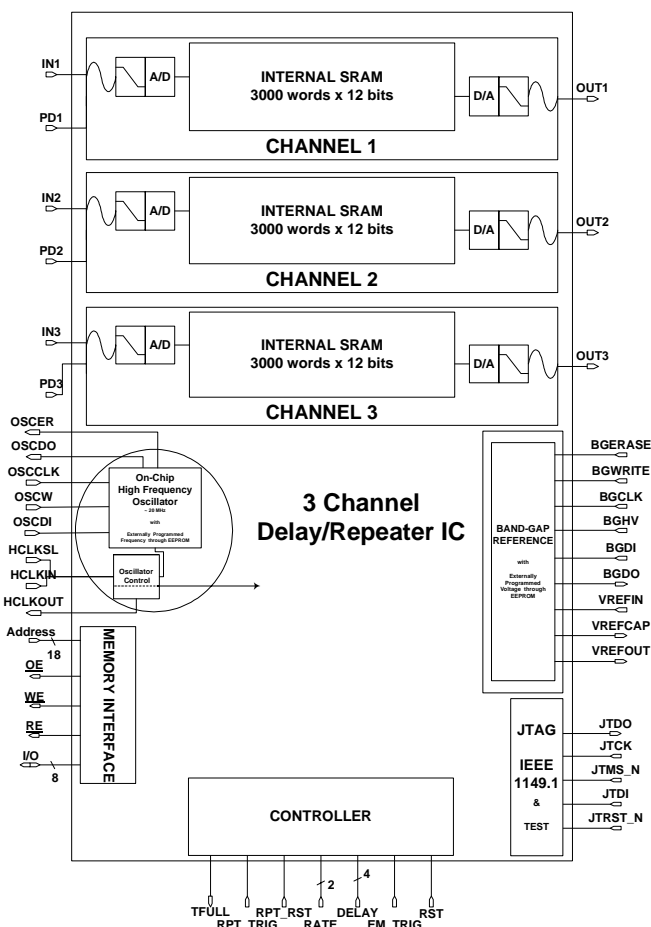


Figure 1: Functional Block Diagram

PROGRAMMING

The 3 Channel Delay/Repeater IC uses discrete signals that may be set using dip switches and/or jumpers to program the input control signals. The following Tables illustrate the D/R's programming functions.

Truth Tables				
TRIG	RST	Function	Rate	Playback Rate
0	0	Power-up FIFO function	00	x1.0
1	0	Repeat function	01	x1.0
0	1	Return to FIFO function	10	x0.5
1	1	No Action	11	x0.1

Internal Memory	
Delay	Time Delay (ms)
0001	5
0010	10
0011	15
0100	20

External Memory	
Delay	Time Delay (ms)
1001	25
1010	50
1011	75
1100	100
1101	125
1110	150
1111	175

SPECIFICATIONS

Parameter	Symbol	Min	Typ	Max	Units
Power Requirements					
Supply Voltage	V_{DD}	4.5	5.0	5.5	V
Supply Current	I_{DD}		50		mA
Power Consumption	I_{PD}		TBD		μ A
			250		mW
			TBD		μ W
Dynamic Specifications					
Operating Ambient Temperature	T_A	-40	25	85	$^{\circ}$ C
External Voltage Reference	V_{EXT}	1.5	2.25	2.5	V
Internal Voltage Reference	V_{REF}	2.13	2.25	2.37	V
Resolution				12	Bits
Clock Frequency	F_C		19.2	20	MHz
Conversion Rate	F_S		150	156	KSPS
Input Frequency Response		DC		60K	Hz
Signal to Noise	S/N	68			dB
Total Harmonic Distortion	THD		0.4	1	%
Interchannel Crosstalk				1.25	mVrms
Interchannel Gain Mismatch				± 0.5	dB
Absolute Gain Error			± 1	± 2	%
Gain Drift			100	200	ppm/ $^{\circ}$ C
Analog Inputs					
Full Scale Input Voltage	IN1-IN3		$1.8 \cdot V_{REF}$	4.2	V
Input Capacitance	C_{INA}			15	pF
Input Resistance	R_{INA}	1M			Ω
Analog Outputs					
Full Scale Output Voltage	OUT1-OUT3		$1.8 \cdot V_{REF}$	4.2	V
Output Resistance	R_{OA}		600	1K	Ω
External Load Capacitance	C_{LA}			100	pF
External Load Resistance	R_{LA}	10K			Ω
Clock					
Duty Ratio	CLK	45	50	55	%
Clock High Voltage	V_{CLKH}	$0.7 \cdot V_{DD}$		V_{DD}	V
Clock Low Voltage	V_{CLKL}	0		$0.3 \cdot V_{DD}$	V
Digital Inputs					
Input High Voltage	V_{INH}	2.4		V_{DD}	V
Input Low Voltage	V_{INL}	0		0.8	V
Input Current	I_{IND}			± 1	μ A
Input Capacitance	C_{IND}			10	pF
Digital Outputs					
Output High Voltage	V_{OHD}	4.0		V_{DD}	V
Output Low Voltage	V_{OLD}	0		0.4	V

	100	
	14x14	
Symbol	MIN.	MAX.
A	-	1.60
A1	0.05	0.15
A2*	1.35	1.45
D	16.00 BSC	
D/2	8.00 BSC	
D1	14.00 BSC	
E	16.00 BSC	
E/2	8.00 BSC	
E1	14.00 BSC	
L	0.45	0.75
e	0.50 BSC	
b	0.17	0.27
c	0.09	0.20

PACKAGING

The Thin Quad Flatpack (TQFP) plastic package family is a reduced thickness plastic surface mount package. The 100 lead TQFP packages are constructed using the latest wire bonding and molding technology to provide surface mount packages with a body thickness of 1.0 or 1.4mm. This package finds many applications where size and weight are a critical factor.

The 3 Channel D/R IC will be available in die form.

